

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C (Package Limited)
80V	3.8mΩ @ V _{GS} = 10V	100A
	5.3mΩ @ V _{GS} = 4.5V	100A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMTH8004LPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Description and Applications

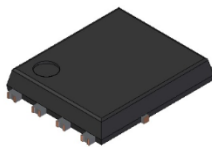
This new generation MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in power management and load switches.

- DC-DC converters
- Load switches

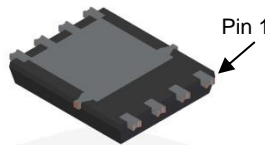
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

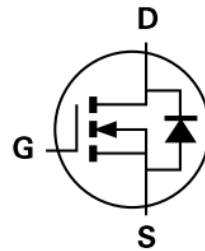
PowerDI5060-8/SWP (Type UX)



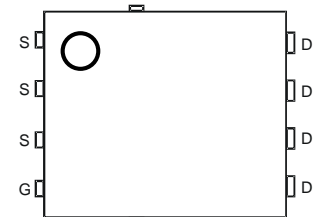
Top View



Bottom View



Internal Schematic



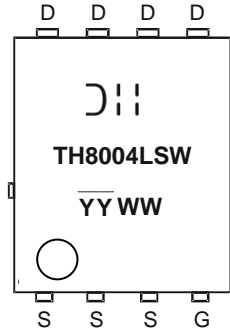
Top View
Pin Configuration

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMTH8004LPSWQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



D;: = Manufacturer's Marking
 TH8004LSW = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 24 = 2024)
 WW = Week (01 to 53)

Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	80	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	Steady State	I _D	100 100	A
Maximum Continuous Body Diode Forward Current (Note 5)		I _S	83	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	400	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	400	A
Avalanche Current, L = 0.3mH (Note 6)		I _{AS}	35	A
Avalanche Energy, L = 0.3mH (Note 6)		E _{AS}	183.7	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R _{θJA}	101	°C/W
Total Power Dissipation (Note 8)	T _A = +25°C	P _D	2.9	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	R _{θJA}	51	°C/W
Total Power Dissipation (Note 5)	T _C = +25°C	P _D	125	W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	1.2	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

- Notes:
5. Thermal resistance from junction to soldering point (on the exposed drain pad).
 6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 7. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 8. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	80	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 64V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1.3	—	2.8	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.8	3.8	mΩ	V _{GS} = 10V, I _D = 20A
		—	3.9	5.3		V _{GS} = 4.5V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	4979	—	pF	V _{DS} = 40V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	1166	—		
Reverse Transfer Capacitance	C _{rss}	—	71	—		
Gate Resistance	R _G	—	2.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	43	—	nC	V _{DD} = 40V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	81	—		
Gate-Source Charge	Q _{gs}	—	14	—		
Gate-Drain Charge	Q _{gd}	—	22	—		
Turn-On Delay Time	t _{D(ON)}	—	8.5	—	ns	V _{DD} = 40V, V _{GS} = 10V I _D = 20A, R _G = 1.6Ω
Turn-On Rise Time	t _R	—	11.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	55	—		
Turn-Off Fall Time	t _F	—	27.7	—		
Body Diode Reverse-Recovery Time	t _{RR}	—	53	—	ns	I _F = 20A, di/dt = 100A/μs
Body Diode Reverse-Recovery Charge	Q _{RR}	—	91	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

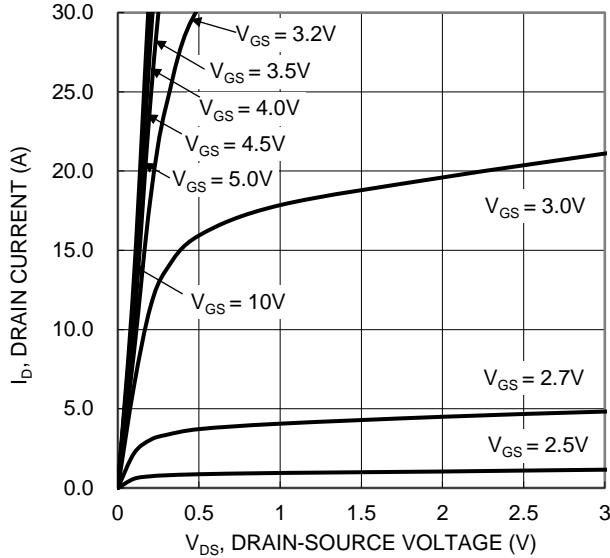


Figure 1. Typical Output Characteristic

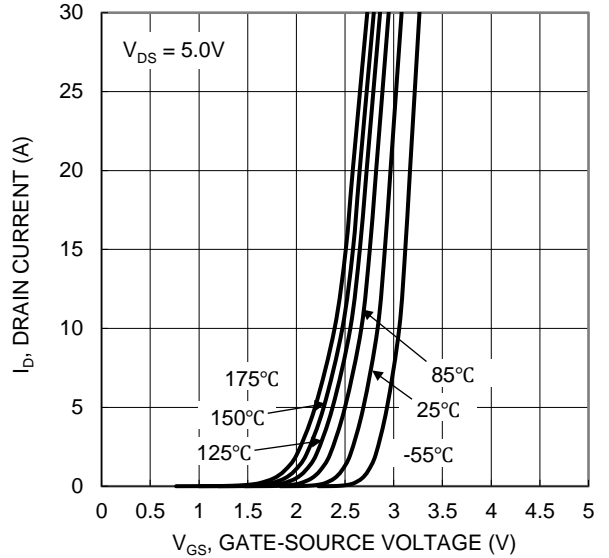


Figure 2. Typical Transfer Characteristic

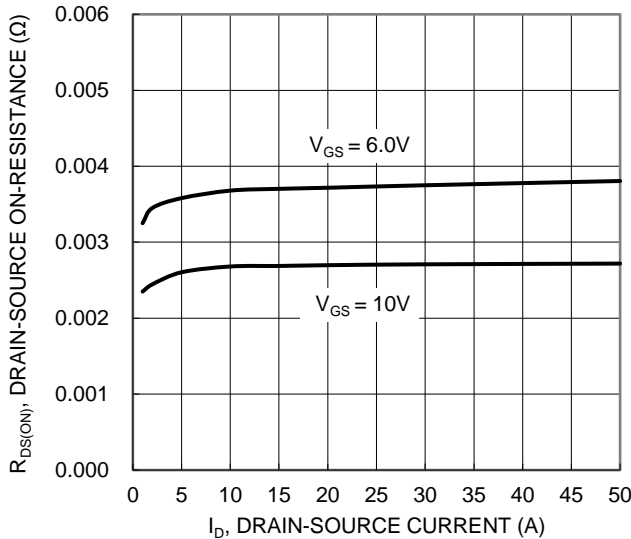


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

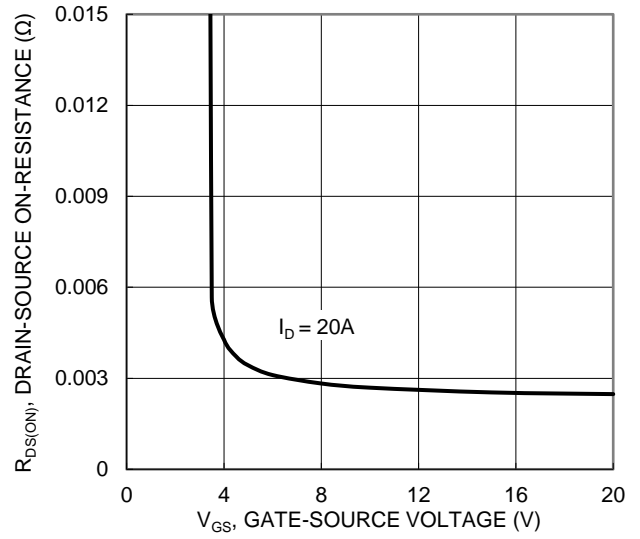


Figure 4. Typical Transfer Characteristic

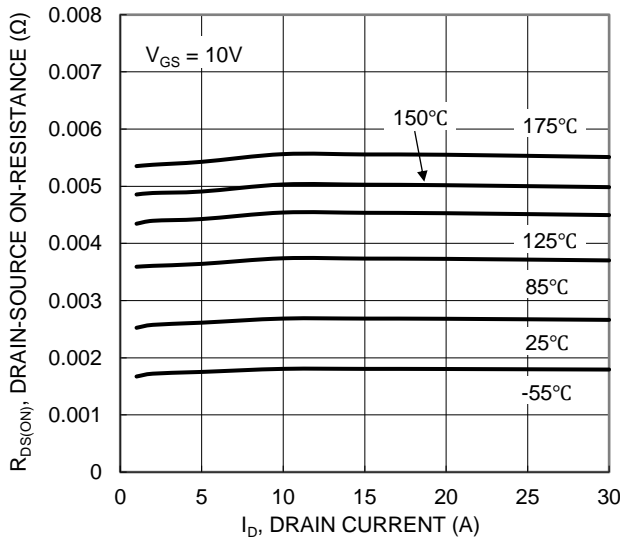


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

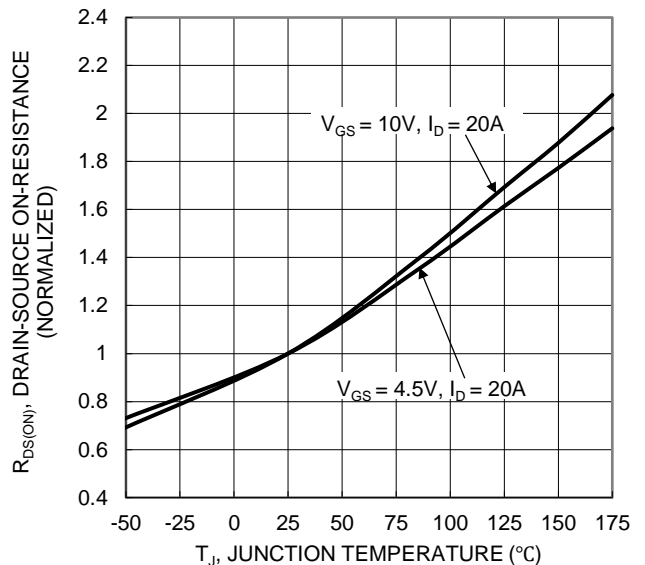


Figure 6. On-Resistance Variation with Temperature

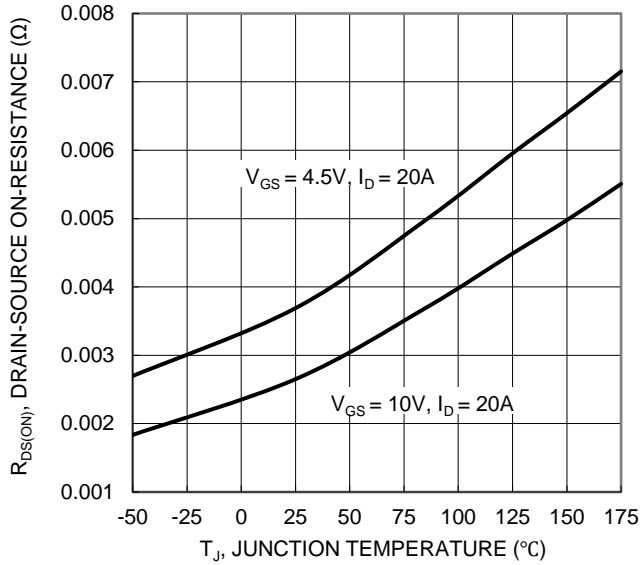


Figure 7. On-Resistance Variation with Temperature

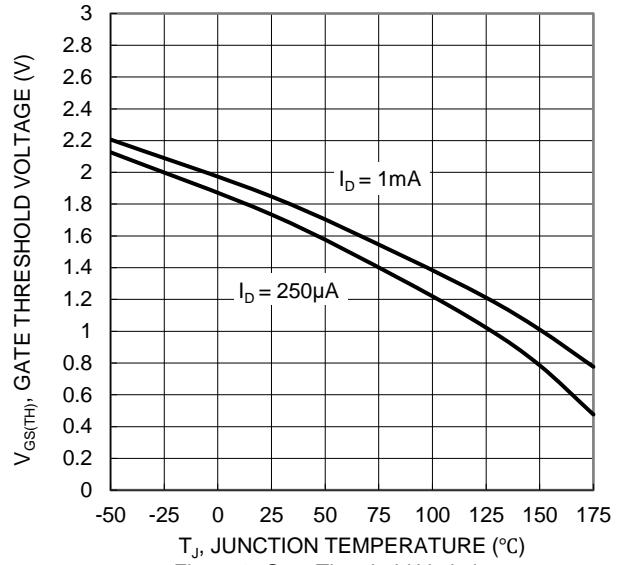


Figure 8. Gate Threshold Variation vs. Junction Temperature

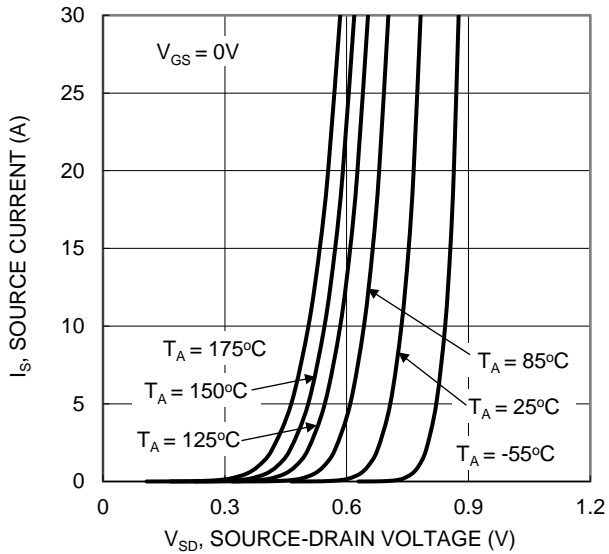


Figure 9. Diode Forward Voltage vs. Current

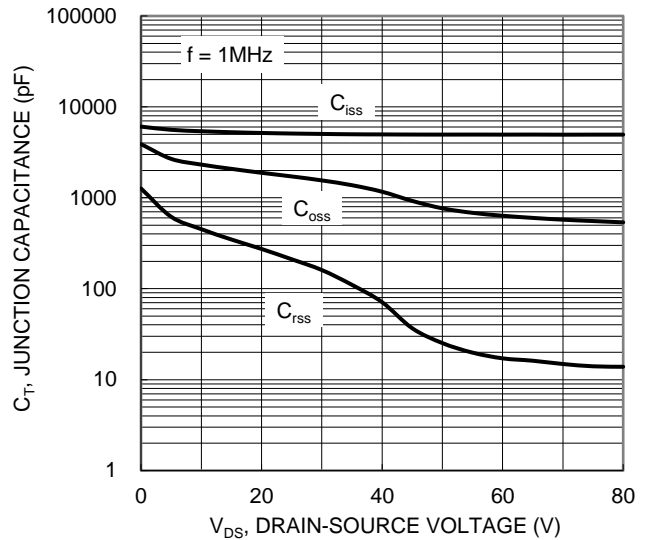


Figure 10. Typical Junction Capacitance

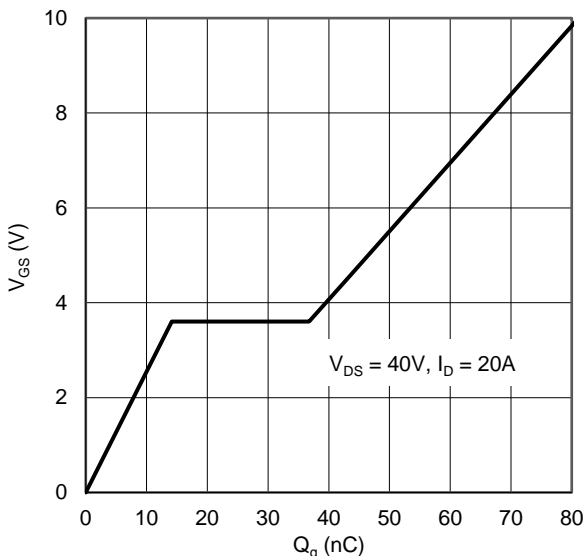


Figure 11. Gate Charge

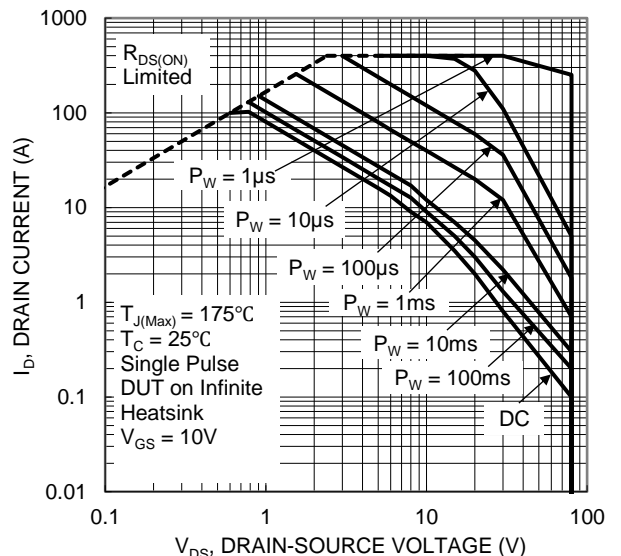


Figure 12. SOA, Safe Operation Area

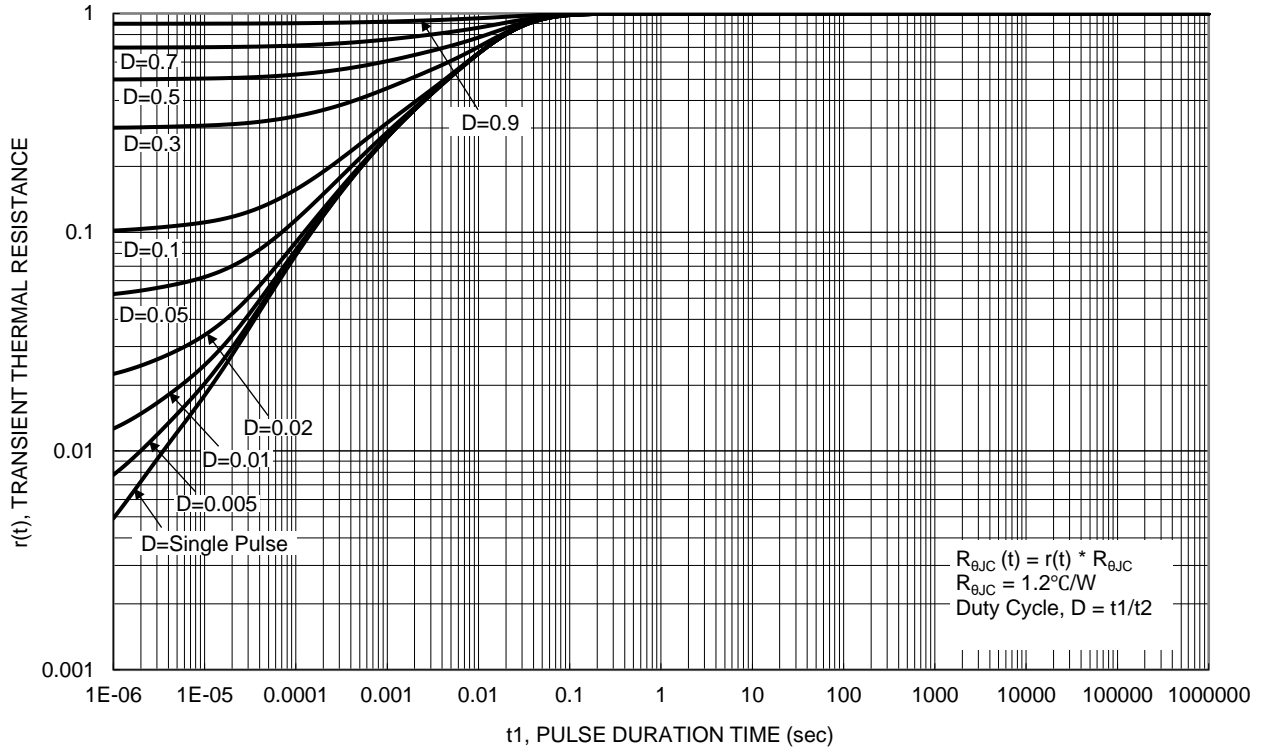


Figure 13. Transient Thermal Resistance

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